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Attorney's Docket No.: 10559-587001 / P12768

GP/2812

#4

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Been-Yih Jin et al.
Serial No. : 10/081,992
Filed : February 21, 2002
Title : NON-SILICON SEMICONDUCTOR AND HIGH-K GATE DIELECTRIC
METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS

Art Unit : 2812
Examiner : Unknown

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INFORMATION DISCLOSURE STATEMENT

Applicants submit the references listed on the attached form PTO-1449, copies of which are enclosed.

This statement is being filed before the receipt of a first Office action on the merits.

Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date:

August 8, 2002

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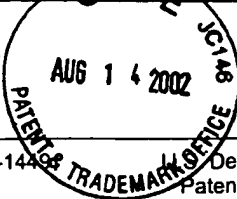
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| Substitute Form PTO-1449 (Modified) Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b)) | Department of Commerce Patent and Trademark Office | Attorney's Docket No. 10559-587001 | Application No. 10/081,992 |
| | | Applicant Been-Yih Jin et al. | |
| | | Filing Date February 21, 2002 | Group Art Unit 2812 |
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| Foreign Patent Documents or Published Foreign Patent Applications | | | | | | | | |
|---|--------------|--------------------|---------------------|-----------------------------|-------|----------|-------------|----|
| Examiner Initial | Desig. ID | Document Number | Publication Date | Country or Patent Office | Class | Subclass | Translation | |
| | | | | | | | Yes | No |
| | AA | | | | | | | |
| | AB | | | | | | | |
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| Other Documents (include Author, Title, Date, and Place of Publication) | | |
|---|--------------|--|
| Examiner Initial | Desig. ID | Document |
| | AF | Chau et al., International Electron Devices Meeting 2000, San Francisco, CA, December 10-13, 2000. |
| | AG | Ghani et al., Symposium on VLSI Technology Digest of Technical Papers, Honolulu, HI, June 13-15, 2000. |
| | AH | Hubbard et al., "Thermodynamic stability of binary oxides in contact with silicon" J. Mater. Res., Vol. 11, No. 11, Nov. 1996. |

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| EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | |